

Vishay Siliconix

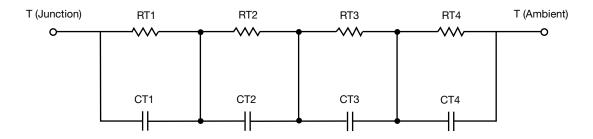
## **R-C Thermal Model Parameters**

#### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in PSpice, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the PSpice simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the PSpice Platform".

#### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK	C VALUES FOR TANK CONFIGURATION				
	THERMAL RES	SISTANCE (°C/W)			
Junction to	Ambient	Case	Foot		
RT1	n/a	131.6686m	n/a		
RT2	n/a	32.8555m	n/a		
RT3	n/a	136.8729m	n/a		
RT4	n/a	148.9584m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	n/a	38.9421m	n/a		
CT2	n/a	22.0277m	n/a		
CT3	n/a	192.6946m	n/a		
CT4	n/a	194.4802m	n/a		

#### Note

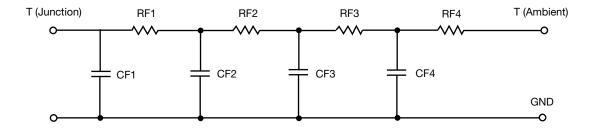
n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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### **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	n/a	45.7669m	n/a		
RF2	n/a	101.0708m	n/a		
RF3	n/a	152.4947m	n/a		
RF4	n/a	151.5912m	n/a		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	n/a	9.6079m	n/a		
CF2	n/a	12.2386m	n/a		
CF3	n/a	17.3612m	n/a		
CF4	n/a	134.2145m	n/a		

#### Note

• n/a indicates not applicable





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